

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1245	361/91.5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/22 09:27
S2	2176	inductive adj load and (FET MOSFET MOS (field adj effect))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 11:16
S3	820	inductive adj load same (FET MOSFET MOS (field adj effect))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:13
S4	43	inductive adj load same (FET MOSFET MOS (field adj effect)) and switch near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:14
S5	3	inductive adj load same (FET MOSFET MOS (field adj effect)) and switch near gate near ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:58
S6	11	inductive adj load same (FET MOSFET MOS (field adj effect)) and switch same gate near ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 16:18
S7	16	("3979607"   "5023692"   "5028811"   "5079608"   "5115369"   "5162966"   "5264736"   "5401996"   "5764088"   "5812006"   "5828244"   "5875089"   "5963066"   "6127746"   "6201427"   "6204715").PN.	USPAT	OR	ON	2004/09/20 15:26
S8	1	inductive adj load same igt and switch same gate near ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:51
S9	1	"5500616".PN.	USPAT	OR	ON	2004/09/20 15:49
S10	3	"5500616".URPN.	USPAT	OR	ON	2004/09/20 15:49
S11	4	inductive adj load same igt and switch same gate near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:52

S12	0	inductive adj load same (FET MOSFET MOS (field adj effect)) and charge adj pump	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:59
S13	46	inductive adj load same (FET MOSFET MOS (field adj effect)) and charge adj pump	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 15:59
S14	4	inductive adj load same (FET MOSFET MOS (field adj effect)) and charge adj pump and gate near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 16:00
S15	778	361/91.1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/20 16:19
S16	8	"5,828,244"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 15:24
S17	7	("3742252"   "4481434"   "4631652"   "4777387"   "5126651"   "5352932"   "5371418").PN.	USPAT	OR	ON	2004/09/21 13:12
S18	0	esd same (FET MOS MOSFET) same gate near drain near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:15
S19	205	esd same (FET MOS MOSFET) same gate same drain same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:29
S20	299	transient same (FET MOS MOSFET) same gate same drain same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:30
S21	1	transient same (FET MOS MOSFET) same gate same drain near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:30

S22	34	transient same (FET MOS MOSFET) same gate near drain same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:31
S23	7	("3742252"   "4481434"   "4631652"   "4777387"   "5126651"   "5352932"   "5371418").PN.	USPAT	OR	ON	2004/09/21 13:49
S24	11	("4356416"   "4459498"   "4500801"   "4677325"   "4716309"   "4719531"   "4737667"   "4816699"   "4859875"   "4928053"   "4952827").PN.	USPAT	OR	ON	2004/09/21 13:51
S25	6	"5828244".URPN.	USPAT	OR	ON	2004/09/21 13:53
S26	126	esd and trigger adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:54
S27	82	esd same trigger adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:55
S28	0	esd same trigger adj circuit near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:55
S29	30	esd same trigger adj circuit same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:57
S30	436556	MOS MOSFET FET and bias adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:58
S31	2193	(MOS MOSFET FET) and bias adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:58
S32	837	(MOS MOSFET FET) same bias adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:58

S33	38	(MOS MOSFET FET) same bias adj resistor same gate near drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 13:59
S34	0	(MOS MOSFET FET) same miller adj effect near resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 14:00
S35	41	(MOS MOSFET FET) same miller adj effect same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 14:00
S36	5	("4916599"   "5457624"   "5552695"   "5847554"   "6304474").PN.	USPAT	OR	ON	2004/09/21 14:07
S37	3144	361/111	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/21 16:04
S38	2070	(FET MOSFET MOS (field adj effect)) near (protect protecting protection)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/10 15:14
S39	8	(FET MOSFET MOS (field adj effect)) near (protect protecting protection) near over adj voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/10 15:25
S40	10	(FET MOSFET MOS (field adj effect)) near (protect protecting protection) near surge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/10 15:26
S41	6	("4744369"   "5079455"   "5122724"   "5374887"   "5930130"   "6438002").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/10 15:30
S42	883	361/91.1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/02/10 15:45
S43	3363	361/111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/02/10 16:18

S44	1073	361/91.5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 09:33
S45	5	"6,005,761"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 13:28
S46	1	("5115225").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 14:08
S47	3	("6005761").URPN.	USPAT	OR	ON	2005/02/21 14:09